## MSKSEMI















**ESD** 

TVS

TSS

MOV

**GDT** 

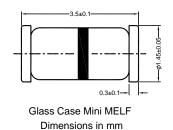
**PLED** 

# Brodnet data speet

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These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.



LL-34

#### **REEL SPECIFICATION**

P/N	PKG	QTY
LLDB3/LLDB4	LL34	2500

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

7.1000 maximum (1.a = 20 0)					
Parameter	Symbol	Value	Unit		
Power Dissipation (T <sub>a</sub> = 65 °C)	P <sub>tot</sub>	150	mW		
Repetitive Peak On-state Current (tp = 20 μs, f = 100 Hz)	I <sub>TRM</sub>	2	А		
Operating Junction and Storage Temperature Range	$T_{j},T_{stg}$	- 40 to + 125	°C		

#### Characteristics at $T_a = 25$ °C

Parameter		Symbol	Min.	Max.	Unit
Breakover Voltage	LLDB3	- V <sub>BO</sub>	28	36	V
at C = 22 nF, see diagram 1	LLDB4		35	45	
Breakover Voltage Symmetry at C = 22 nF, see diagram 1		[ +V <sub>BO</sub>  - -V <sub>BO</sub>  ]	-	3	V
Dynamic Breakover Voltage at $\Delta I = [I_{BO} \text{ to } I_F = 10 \text{ mA}]$		ΔV ±	5	-	V
Output Voltage See diagram 2		Vo	5	-	V
Breakover Current at C = 22 nF		I <sub>BO</sub>	-	50	μΑ
Leakage Current at $V_B = 0.5 V_{BO}$ max		I <sub>B</sub>	-	10	μΑ
Rise Time See diagram 3		t <sub>r</sub>	-	2	μs



Diagram 1: Current-voltage characteristics

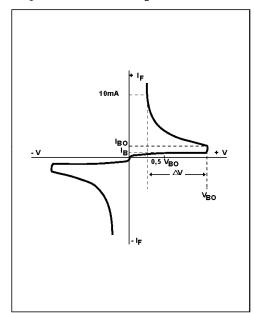


Diagram 2: Test circuit for output voltage

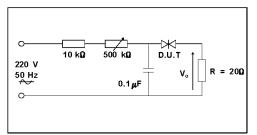


Diagram 3: Test circuit see diagram 2. Adjust R for Ip=0.5A

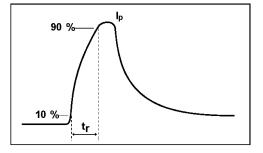


Fig. 1: Power dissipation versus ambient temperature (maximum values)

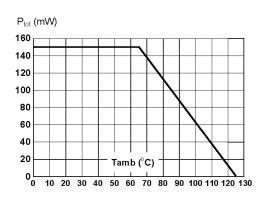


Fig. 2: Relative variation of V<sub>BO</sub> versus junction temperature (typical values)

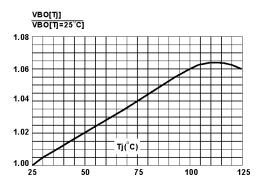
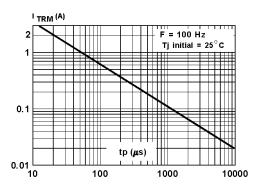


Fig. 3: Peak pulse current versus pulse duration (maximum values)





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